

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	8	US-6318175-\$ DID. OR US-5922212-\$ DID. OR US-5683591-\$ DID. OR US-5804083-\$ DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 06:47
S2	2	("20040248344").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/02 07:39
S3	225	"partridge, aaron" or "Lutz, Markus" or "Kronmueller, Silvia".in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 08:16
S4	13	S3 and Silicon adj oxide adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 08:17
S5	18544	robert adj bosch.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 08:29
S6	57	S5 and silicon adj oxide adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 08:29
S7	0	S5 and silicon adj oxide adj layer and oxidiz\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 08:30
S8	11	S5 and silicon adj oxide adj layer and oxidiz\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 08:30
S9	88	silicon adj oxide adj layer and oxidiz\$3 and heat\$3	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/02 08:47
S10	2	silicon adj oxide adj layer and oxidiz\$3 and heat\$3 and sacrifice\$3	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/02 08:48
S11	5473	silicon adj oxide adj layer and oxidiz\$3 and heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 09:03
S12	167	silicon adj oxide adj layer and oxidiz\$3 and heat\$3 and anneal\$3 and (vent or gap) and sacrifice\$3 and etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 09:05

S14	4	S12 and encapsulat\$3 adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 09:06
S15	223	(silicon adj oxide adj layer) same oxidiz\$3 same (anneal\$3 or heat) and (vent or gap) and etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 09:12
S16	1	(silicon adj oxide adj layer) same oxidiz\$3 same (anneal\$3 or heat) same (vent or gap) same etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 09:12
S17	7	(silicon adj oxide adj layer) same oxidiz\$3 same (anneal\$3 or heat) same (vent or gap) and etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 09:13
S18	7	("4666556" l "5447884" l "5665635" l "5726090" l "5731241" l "5741740" l "6097076").PN. OR ("6417071").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/02 09:45
S24	1	(silicon adj oxide adj layer) same oxidiz\$3 and (anneal \$3 or heat) and (vent or gap) and electrochemical adj device	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 10:41
S27	1	(silicon adj oxide adj layer) same (anneal\$3 or heat) and (vent or gap) and (\$selectrochemical adj (device or system))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 10:50
S28	12	(oxide adj layer) same (anneal\$3 or heat) and (vent or gap) and (\$selectrochemical adj (device or system))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 10:52
S29	6	((10454867") or ("10455555") or ("10018180") or ("10240339")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/02 11:39
S30	2	("20040248344").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/02 11:43
S31	6	(("20040245586") or ("20030049878") or ("20030173330")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/02 11:44
S32	78	("4950624" l "5410176" l "5518959" l "5536681" l "5665635").PN. OR ("5741740").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/02 12:07
S33	336	438/24 ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 12:59

S34	468192	S33 and (microelectromechanical adj system) or MEMS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 13:00
S35	8	S33 and (microelectromechanical adj system)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 13:00
S36	25	S33 and MEMS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 13:01
S37	93	((5426070") or ("5783749") or ("5804084") or ("5843832") or ("5880921") or ("5946176") or ("6040935") or ("6046066") or ("6060336") or ("6074890") or ("6078103") or ("6087701") or ("6149190") or ("6156652") or ("6170332") or ("6180536") or ("6199874") or ("6218205") or ("6218205") or ("6229684") or ("6238580") or ("6238581") or ("6239473") or ("6275325") or ("6342430") or ("6356689") or ("6363712") or ("6372655") or ("6379989") or ("6391788") or ("6420740") or ("6444138") or ("6458718") or ("6461888") or ("6462391") or ("6464892") or ("6465355") or ("6480646") or ("6515898") or ("6518192") or ("6525352") or ("6528887") or ("6534413") or ("6541831") or ("6544655") or ("6582985") or ("6586841") or ("6587613") or ("6600644") or ("6633509").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/02 13:14
S38	18	((5362526") or ("5393708") or ("5462899") or ("5472904") or ("5674783") or ("5702977") or ("5714740") or ("5855957") or ("5869384").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/02 13:59
S39	7	Silicon adj oxide adj layer and (low adj internal adj stress) and dop\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 15:42
S40	1	(Silicon adj oxide adj layer) same dop\$3 and (low adj internal adj stress)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 15:44
S41	5788	(Silicon adj oxide adj layer) same dop\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 15:44
S42	970	(Silicon adj oxide adj layer) same dop\$3 and stress	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 15:45
S43	51	(Silicon adj oxide adj layer) same (dop\$3 with gas) and stress	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/02 15:45

S44	474343	((Sselectromechanical adj system) or MEMS)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 07:46
S45	3890	S44 and "438".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 07:46
S46	87	S45 and (silicon adj oxide) same (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 07:47
S47	28	((Sselectromechanical adj system) or MEMS) same (silicon adj oxide) same (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 07:48
S48	12	(("6808952") or ("5134303") or ("5804084") or ("6082208") or ("6133670") or ("6267605")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/03 08:18
S49	7	("5134303" "5248889" "5804084" "6082208" "6133670" "6267605").PN. OR ("6808952").URPN.	US-PGPUB; USPAT; USOCR;	OR	ON	2008/01/03 08:41
S50	1455	438/48.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 08:43
S51	276	S50 and S44	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 08:44
S52	92	S51 and (Silicon adj oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 08:44
S53	44	S52 and (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 08:44
S54	0	(silicon adj oxide adj layer) and ((vapor or wet or plasma) near etch) same (HF or hydrogen adj fluoride) and residue	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 10:26
S55	2	(silicon adj oxide adj layer) and ((vapor or wet or plasma) near etch) same (HF or hydrogen adj fluoride)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 10:27
S56	6	(silicon adj oxide adj layer) and ((vapor or wet or plasma) near etch) and (HF or hydrogen adj fluoride)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 10:38
S57	9	(silicon adj oxide adj layer) and ((vapor or wet or plasma) with etch) and (HF or hydrogen adj fluoride)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 11:16
S58	21	residue and ((vapor or wet or plasma) with etch) and (HF or hydrogen adj fluoride)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 11:25

S59	15	(("3524817") or ("4370197") or ("4477364") or ("4588471") or ("4970014") or ("5091053")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/03 11:53
S60	0	residue with oxidizS3 and ((vapor or wet or plasma) with etch) and (HF or hydrogen adj fluoride)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 13:35
S61	14	residue with oxidizS3 and ((vapor or wet or plasma) with etch)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/03 13:35
S62	1827	((S5electromechanical adj system) or MEMS) and (sacrificS3 same oxide same layer) and (annealS3 or heatS3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 14:33
S63	353	((S5electromechanical adj system) or MEMS) same (sacrificS3 same oxide same layer) same (annealS3 or heatS3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 14:34
S64	2	((S5electromechanical adj system) or MEMS) same (sacrificS3 same oxide same layer) same (annealS3 or heatS3) and encapsulatS3 near layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 14:34
S65	209	S44 and 438/106.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 14:39
S66	5	S65 and (encapsulatS3 or sacrificS3) adj oxide adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/03 14:40
S67	21	(("5589082") or ("5668033") or ("5783749") or ("5937275") or ("5952572") or ("6140144") or ("6232150") or ("6265246") or ("6297072") or ("6335224")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/03 14:44
S68	0	(microelectromechanical adj system or MEMS) and (heatS3 or annealS3) and (vent or window or trench) and etch and (silicon adj oxide or SiO or "SiO.sub.2")	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/04 15:00
S69	6	(microelectromechanical adj system or MEMS) and (heatS3 or annealS3) and (silicon adj oxide or SiO or "SiO.sub.2")	FPRS; EPO; JPO; DERWENT	OR	ON	2008/01/04 15:01
S70	6875	216/58,72,73,75,79 ccls. or 438/424,425,427,706,734,735.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:02
S71	0	S68 and S70	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:02
S72	1617	(microelectromechanical adj system or MEMS) and (heatS3 or annealS3) and (vent or window or trench) and etch and (silicon adj oxide or SiO or "SiO.sub.2")	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:03
S73	701	(microelectromechanical adj system or MEMS) and (heatS3 or annealS3) and (silicon adj oxide or SiO or "SiO.sub.2")and (vent or window or trench) same etch	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:04
S74	32	S70 and S73	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:04

S75	104	((microelectromechanical adj system or MEMS) and damascene and (heat\$3 or anneal\$3) and (silicon adj oxide or SiO or "SiO.sub.2") and (vent or window or trench) same etch	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:14
S76	0	S70 and S75	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:15
S77	701	((microelectromechanical adj system or MEMS) and (heat\$3 or anneal\$3) and (silicon adj oxide or SiO or "SiO.sub.2") and (vent or window or trench) same etch	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:20
S78	13	((microelectromechanical adj system or MEMS) and (heat\$3 or anneal\$3) same (silicon adj oxide or SiO or "SiO.sub.2") same (vent or window or trench) same etch	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/04 15:24
S79	0	("20020190319A1").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 07:08
S80	2	"20020190319".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 07:08
S81	3	("6946314").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 07:10
S82	8894	216/58,72,73,75,79.ccls. or 438/48,424,425,427,706,734,735,761.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 07:45
S83	13	((microelectromechanical adj system or MEMS) and (heat\$3 or anneal\$3) same (silicon adj oxide or SiO or "SiO.sub.2") same (vent or window or trench) same etch	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 07:45
S84	2	S82 and S83	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 07:45
S85	80	((microelectromechanical adj system or MEMS) and (heat\$3 or anneal\$3) same (silicon adj oxide or SiO or "SiO.sub.2") same (vent or window or trench)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 07:53
S86	5	"20040248344"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:01
S87	0	"20040248344.did."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:03
S88	2	"20040248344".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:03
S89	1653	Selectromechanical and (encapsulat\$5 or packag\$5 or seal\$5)	EPO; JPO; DERWENT	OR	ON	2008/01/07 10:58
S90	19	Selectromechanical and (encapsulat\$5 or packag\$5 or seal\$5) and sacrific\$5 and etchs3	EPO; JPO; DERWENT	OR	ON	2008/01/07 10:59

S91	0	Selectromechanical and (encapsulat\$5 or packag\$5 or seal\$5) and sacrific\$5 and etch\$3 and anneal\$3	EPO; JPO; DERWENT	OR	ON	2008/01/07 11:11
S92	10	(anneal\$3 near3 sacrificial) and sacrificial near3 (oxide or sio2 or "sio.sub.2")	EPO; JPO; DERWENT	OR	ON	2008/01/07 11:25
S93	218	encapsulat\$3 and sacrific\$3	EPO; JPO; DERWENT	OR	ON	2008/01/07 11:42
S94	864332	encapsulat\$3 and sacrific\$3 and silicon oxide or Sio or Sio2 or "Sio.sub.2"	EPO; JPO; DERWENT	OR	ON	2008/01/07 11:42
S95	32	encapsulat\$3 and sacrific\$3 and (silicon oxide or Sio or Sio2 or "Sio.sub.2")	EPO; JPO; DERWENT	OR	ON	2008/01/07 11:43
S96	1	2007-385719.NRAN	DERWENT	OR	ON	2008/01/07 11:45
S97	0	"20010952626".did.	EPO; JPO; DERWENT	OR	ON	2008/01/07 12:37
S98	0	(anneal\$3 near3 sacrific\$3).clm. and sacrific\$3 near3 (oxide or sio2 or "sio.sub.2" or sio)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:08
S99	21	(anneal\$3 near3 sacrific\$3).clm. and sacrific\$3 near3 (oxide or sio2 or "sio.sub.2" or sio)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:10
S100	16	(anneal\$3 near3 sacrific\$3).clm. and sacrific\$3 near3 (oxide or sio2 or "sio.sub.2" or sio) same anneal\$3	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:18
S101	11649	216/2,58,72,73,75,79.ccls. or 438/48,424,425,427,455-456,706,734,735,761.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:31
S102	1696	S101 and (Selectrochemical or MEMS)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:32
S103	830	S102 and (encapsulat\$5 or packag\$4 or seal\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:32
S104	306	S102 and (encapsulat\$5 or packag\$4 or seal\$3) and sacrific\$3 and (etch\$3 or remov\$5)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:34
S105	265	S102 and (encapsulat\$5 or packag\$4 or seal\$3) and (sacrific\$3 near3 layer) and (etch\$3 or remov\$5)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:35
S106	245	S102 and (encapsulat\$5 or packag\$4 or seal\$3) and (sacrific\$3 near3 layer) same (etch\$3 or remov\$5)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/07 13:35
S116	4	(("5589082") or ("5668033")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 16:45
S117	2	("5576250").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/08 06:52
S118	4	(("5285131") or ("5493177")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/08 07:16
S119	2	"20020190319". did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/08 07:33
S120	11654	216/2,58,72,73,75,79.ccls. or 438/48,424,425,427,455-456,706,734,735,761.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 07:33

S121	136	S120 and (Selectromechanical or MEMS) and (encapsulat\$5 or packag\$4 or seal\$3) and (sacrific\$3 near3 layer) same (etch\$3 or remov\$5) and ((anneal or heat) near S119 sacrific\$3).clm	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 07:33
S122	243	S120 and (Selectromechanical or MEMS) and (encapsulat\$5 or packag\$4 or seal\$3) and (sacrific\$3 near3 layer) same (etch\$3 or remov\$5) and ((anneal or heat) near S119 sacrific\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 07:33
S123	83	S120 and (Selectromechanical or MEMS) and (encapsulat\$5 or packag\$4 or seal\$3) same (sacrific\$3 near3 layer) same (etch\$3 or remov\$5) same ((anneal or heat) near S119 sacrific\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 07:51
S124	4	"20040065932".did. or "6635509".pn. or "20020016058".did. or "20030215974".did.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 08:03
S125	2	"19961578".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/08 08:20
S126	2	pct/de00/04454.pct.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/08 11:49
S127	11654	216/2,58,72,73,75,79.ccls. or 438/48,424,425,427,455-456,706,734,735,761.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 14:07
S128	100	S127 and (Selectrochemical or MEMS) and (polycrystalline with silicon) and (monocrystalline with silicon)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 14:07
S129	7	S127 and (Selectrochemical or MEMS) and (polycrystalline with silicon) same (monocrystalline with silicon) same encapsulat\$3	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 14:08
S130	260	S127 and (Selectrochemical or MEMS) and (anneal\$3 or Heat\$3) same (oxygen or "O. _{sub} 2")	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 14:29
S131	38	S127 and (Selectrochemical or MEMS) and (anneal\$3 or Heat\$3) same (oxygen or "O. _{sub} 2") same (ambient \$1 or environment)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 14:30
S132	138638	S127 and (Selectrochemical or MEMS) and ((polycrystalline or amorphous or carbide) near2 silicon or germanium or gallium arsenide	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 15:15
S133	805	S132 and encapsulat\$4 same seal	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 15:16
S134	53	S133 and S127	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 15:16
S135	39	S127 and (Selectrochemical or MEMS) and ((polycrystalline or amorphous or carbide) near2 silicon or germanium or gallium arsenide) same (encapsulat\$3 or seal)	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/08 15:18
S136	3	(Selectrochemical or MEMS) and (polycrystalline with silicon) and (monocrystalline with silicon)	EPO; JPO; DERWENT	OR	ON	2008/01/08 15:56
S137	730	polycrystalline and monocrystalline and silicon	EPO; JPO; DERWENT	OR	ON	2008/01/08 15:58
S138	8	polycrystalline and monocrystalline and silicon and encapsulat\$3	EPO; JPO; DERWENT	OR	ON	2008/01/08 15:59

1/9/2008 6:44:37 AM

C:\Documents and Settings\lsmith2\My Documents\EAST\Workspaces\Crack 10713172.wsp